

#### Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <a href="http://www.nxp.com">http://www.nxp.com</a>, <a href="http://www.semiconductors.philips.com/">http://www.nxp.com</a>, <a href="http://www.nexperia.com/">http://www.nexperia.com/</a>, <a href="http://www.nexperia.com/">use http://www.nexperia.com/</a>

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use salesaddresses@nexperia.com (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

## **DISCRETE SEMICONDUCTORS**

# DATA SHEET

# **PDTA143T series** PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

Product data sheet Supersedes data of 2003 Sep 08 2004 Aug 04



# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

### PDTA143T series

#### **FEATURES**

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

#### **APPLICATIONS**

- General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

#### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
R1	bias resistor	4.7	_	kΩ
R2	open	_	_	_

#### **DESCRIPTION**

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

#### **PRODUCT OVERVIEW**

TVDE NUMBER	PAC	(AGE	MARKING CODE	NDN COMPLEMENT
TYPE NUMBER	PHILIPS	EIAJ	MARKING CODE	NPN COMPLEMENT
PDTA143TE	SOT416	SC-75	39	PDTC143TE
PDTA143TEF	SOT490	SC-89	10	PDTC143TEF
PDTA143TK	SOT346	SC-59	45	PDTC143TK
PDTA143TM	SOT883	SC-101	E6	PDTC143TM
PDTA143TS	SOT54 (TO-92)	SC-43	TA143T	PDTC143TS
PDTA143TT	SOT23	ı	*42 <sup>(1)</sup>	PDTC143TT
PDTA143TU	SOT323	SC-70	*45 <sup>(1)</sup>	PDTC143TU

#### Note

<sup>1. \* =</sup> p: Made in Hong Kong.

<sup>\* =</sup> t: Made in Malaysia.

<sup>\* =</sup> W: Made in China.

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

# PDTA143T series

### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CYMPOL		PINNING
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION
PDTA143TS	1 R1 R1 3 MAM362	1 2 3	base collector emitter
PDTA143TE PDTA143TEF PDTA143TK PDTA143TT PDTA143TU	3 1 R1 3 1 DDB272	1 2 3	base emitter collector
PDTA143TM	2 R1 3 1 Bottom view  MDB268	1 2 3	base emitter collector

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

### PDTA143T series

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
Io	output current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT23	note 1	_	250	mW
	SOT54	note 1	_	500	mW
	SOT323	note 1	_	200	mW
	SOT346	note 1	_	250	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### **Notes**

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT23	note 1	500	K/W
	SOT54	note 1	250	K/W
	SOT323	note 1	625	K/W
	SOT346	note 1	500	K/W
	SOT416	note 1	833	K/W
	SOT490	note 1	500	K/W
	SOT883	notes 2 and 3	500	K/W

#### **Notes**

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu m$  copper strip line.

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

# PDTA143T series

#### **CHARACTERISTICS**

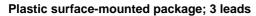
 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ mA}$	200	_	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	_	_	-150	mV
R1	input resistor		3.3	4.7	6.1	kΩ
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	_	3	pF

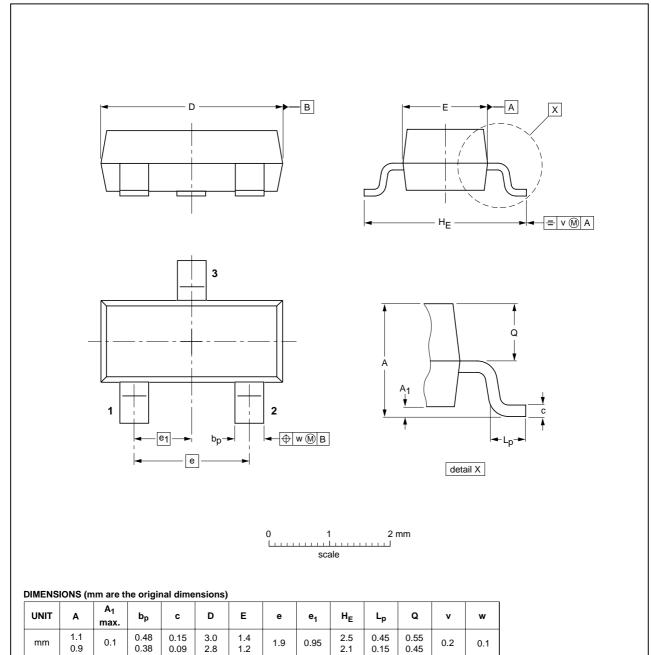
# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

## PDTA143T series

#### **PACKAGE OUTLINES**



SOT23



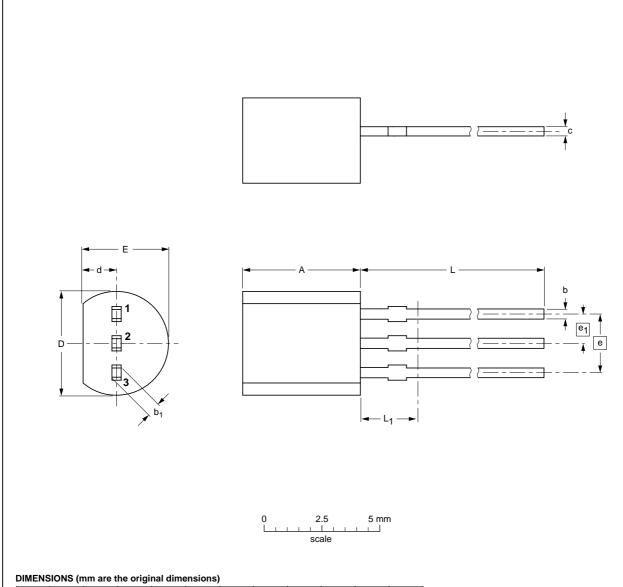
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION		
SOT23		TO-236AB			<del>04-11-04</del> 06-03-16	
SO123		TO-236AB			06-03	

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

## PDTA143T series

#### Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

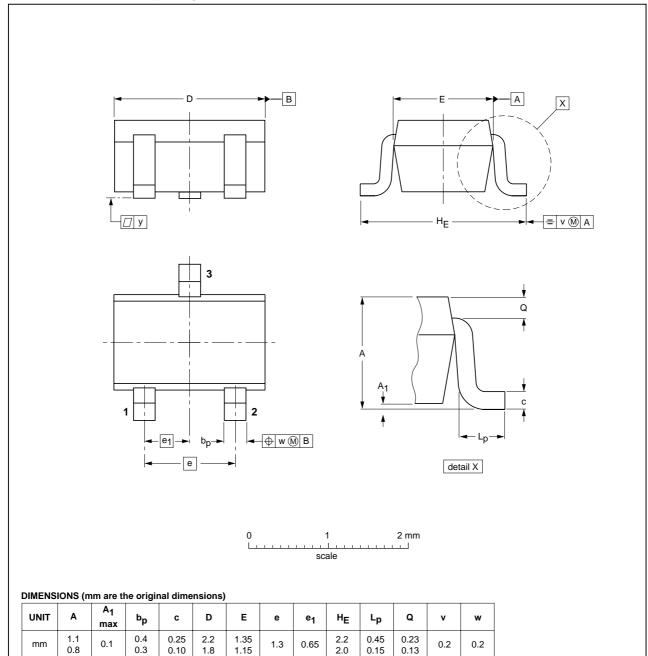
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A			<del>-04-06-28</del> 04-11-16	

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

## PDTA143T series

#### Plastic surface-mounted package; 3 leads

SOT323



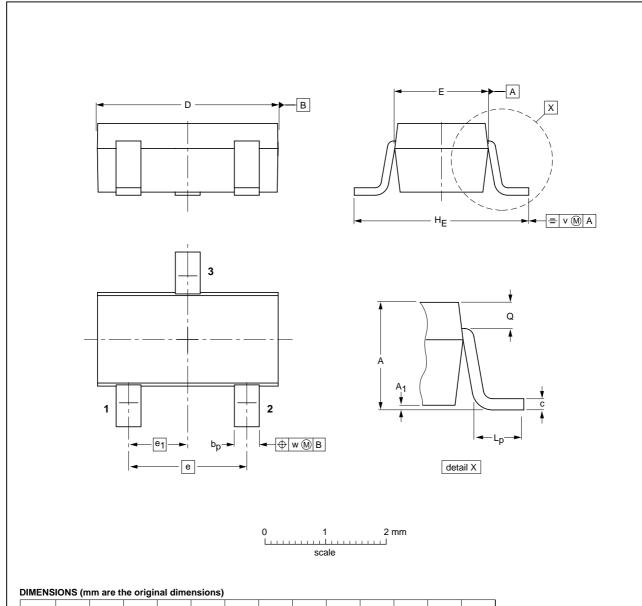
OUTLINE		ES		ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT323			SC-70			<del>04-11-04</del> 06-03-16	

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

## PDTA143T series

### Plastic surface-mounted package; 3 leads

SOT346



UNIT	Α	A <sub>1</sub>	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

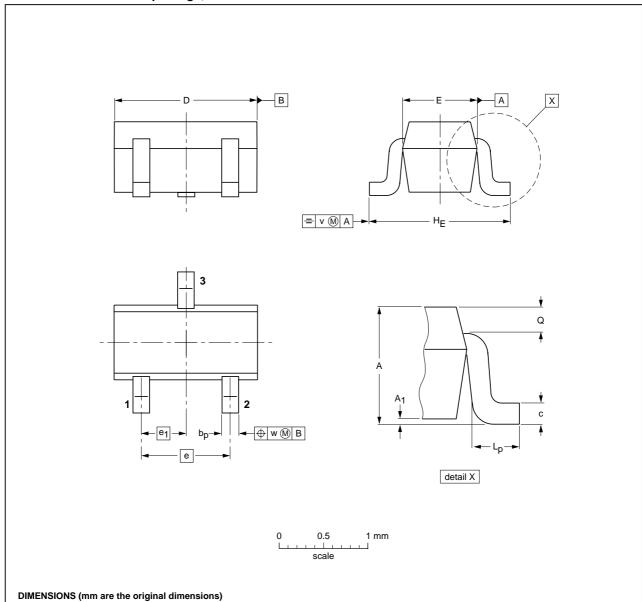
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT346		TO-236	SC-59A		<del>04-11-11</del> 06-03-16	

# PNP resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$ , R2 = open

## PDTA143T series

#### Plastic surface-mounted package; 3 leads

**SOT416** 



UNIT	Α	A <sub>1</sub> max	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	ø	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION		
SOT416			SC-75		<del>04-11-04</del> 06-03-16	

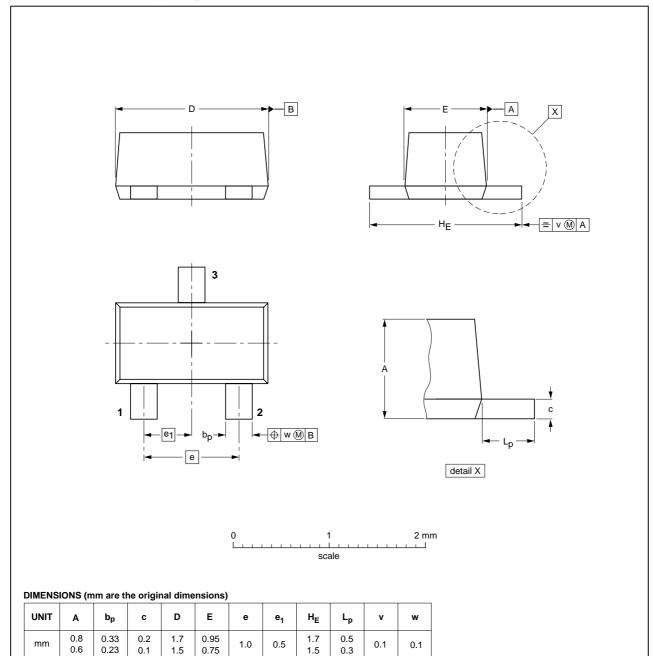
2004 Aug 04 10

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

## PDTA143T series

#### Plastic surface-mounted package; 3 leads

SOT490



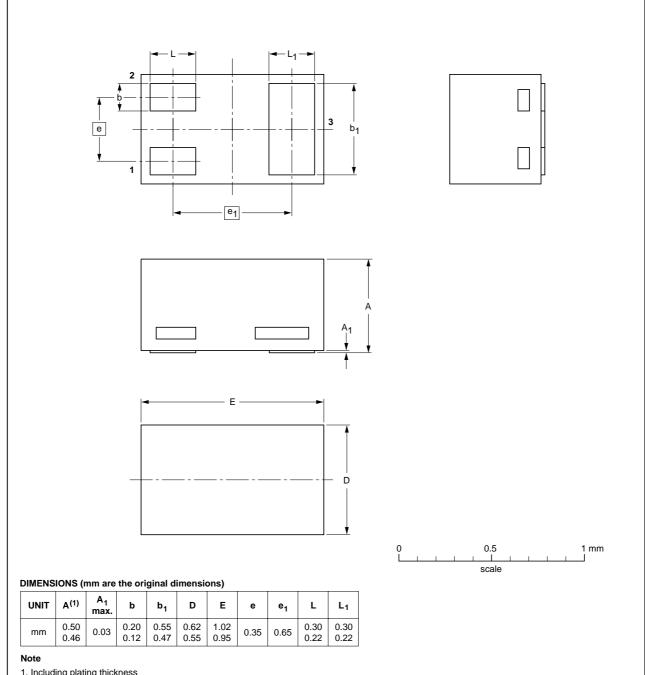
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT490			SC-89		<del>05-07-28</del> 06-03-16

# PNP resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$ , R2 = open

## PDTA143T series

#### Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

**SOT883** 



1. Including plating thickness

OUTLINE		REFER	REFERENCES			ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT883			SC-101			<del>03-02-05</del> 03-04-03	

2004 Aug 04 12

## PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

### PDTA143T series

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

#### **DISCLAIMERS**

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and

operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

## **NXP Semiconductors**

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands R75/04/pp14 Date of release: 2004 Aug 04 Document order number: 9397 750 13656

